

<b>SANYO</b>	No.3580A	<b>2SC4696</b>
		NPN Epitaxial Planar Silicon Darlington Transistor

**Driver Applications**

**Applications**

- Motor drivers, printer hammer drivers.

**Features**

- Darlington connection.
- On-chip Zener diode of  $90 \pm 10V$  between collector and base.
- High DC current gain.
- High inductive load handling capability.

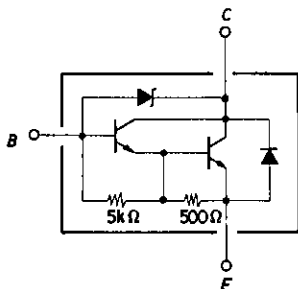
**Absolute Maximum Ratings at  $T_a = 25^\circ C$**

				unit
Collector-to-Base Voltage	$V_{CBO}$	With a low-voltage diode ( $90 \pm 10V$ )	80	V
Collector-to-Emitter Voltage	$V_{CEO}$	With a low-voltage diode ( $90 \pm 10V$ )	80	V
Emitter-to-Base Voltage	$V_{EBO}$		6	V
Collector Current	$I_C$		0.8	A
Collector Current (Pulse)	$I_{CP}$		1.5	A
Base Current	$I_B$		0.1	A
Collector Dissipation	$P_C$		1.0	W
Junction Temperature	$T_j$		150	$^\circ C$
Storage Temperature	$T_{stg}$		-55 to +150	$^\circ C$

**Electrical Characteristics at  $T_a = 25^\circ C$**

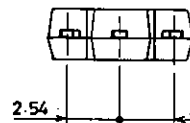
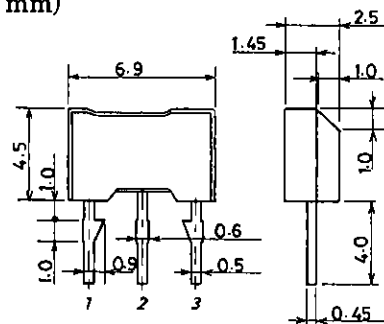
			min	typ	max	unit
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = 60V, I_E = 0$			10	$\mu A$
Emitter Cutoff Current	$I_{EBO}$	$V_{EB} = 5V, I_C = 0$			2	mA
DC Current Gain	$h_{FE}$	$V_{CE} = 3V, I_C = 500mA$	1000		20000	
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = 500mA, I_B = 1mA$		0.95	1.5	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = 500mA, I_B = 1mA$		1.5	2.0	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 100\mu A, I_E = 0$	80		100	V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 1mA, R_{BE} = \infty$	80		100	V
Inductive Load Handling Capability	Es/b	$L = 30mH, R_{BE} = 100\Omega$	25			mJ

**Electrical Connection**



**Package Dimensions 2064A**

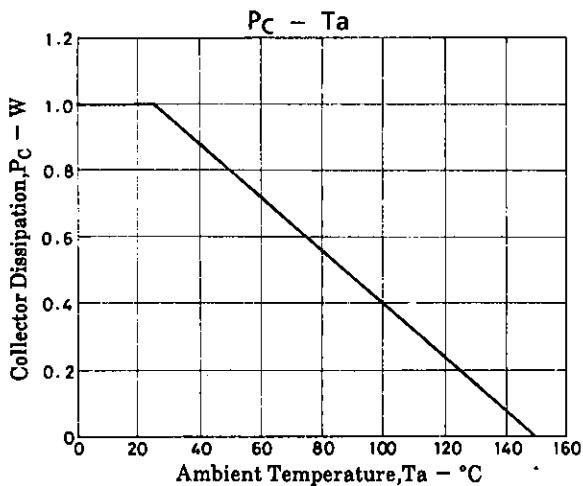
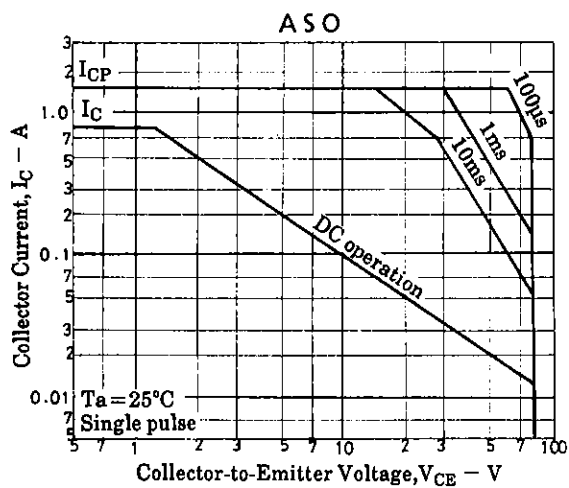
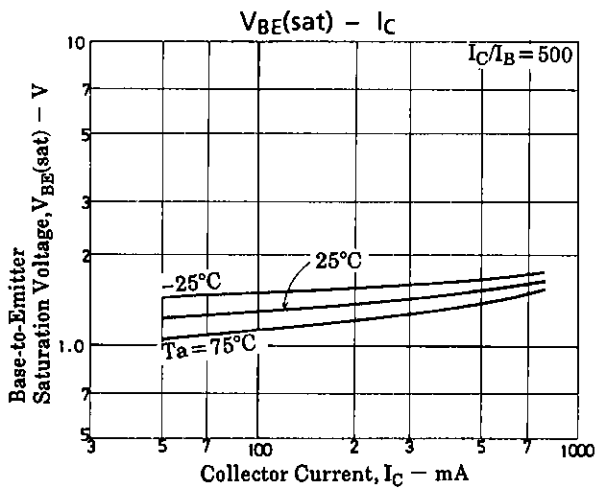
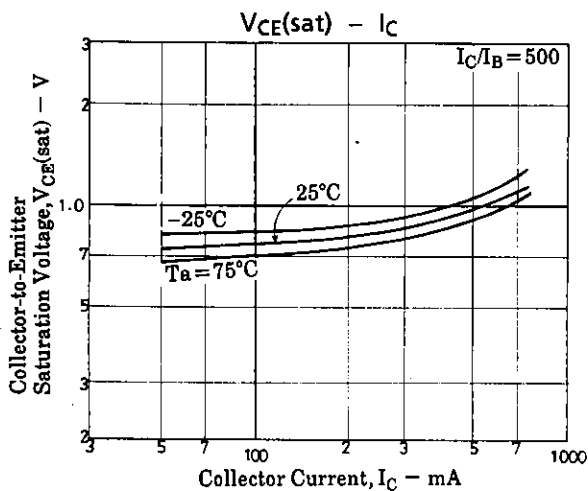
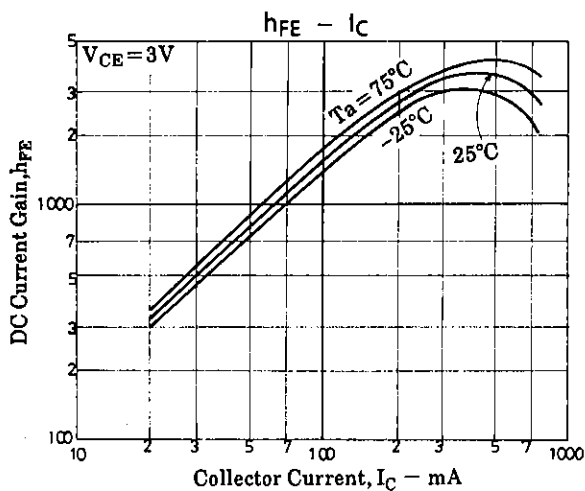
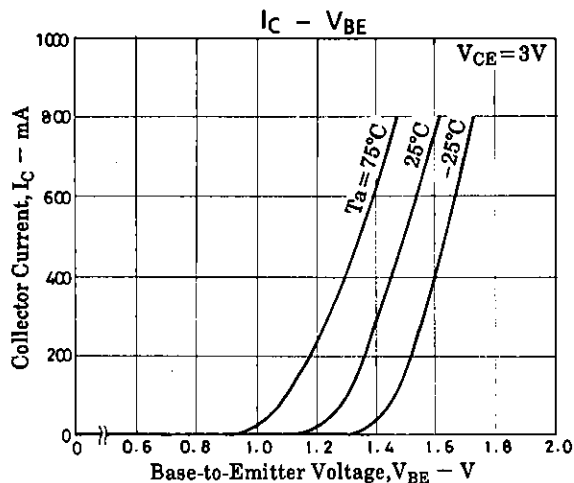
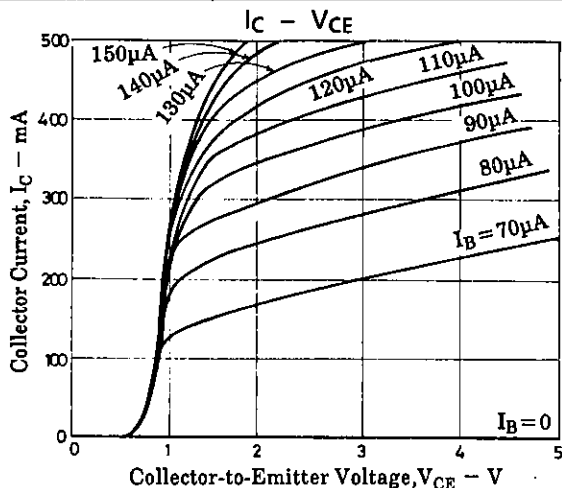
(unit : mm)



- 1 : Emitter
- 2 : Collector
- 3 : Base

SANYO : NMP

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